MOSFET - N-Channel
Shielded Gate PowerTrench®
150 V, 15 mΩ, 61.3 A

NVDS015N15MC

Features

- Shielded Gate MOSFET Technology
- Max $R_{DS(on)}$ = 15 mΩ at V_{GS} = 10 V, I_D = 29 A
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- Primary Side for 48 V Isolated Bus
- SR for MV Secondary Applications

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	150	V
Gate−to−Source Voltage			V_{GS}	±20	V
Continuous Drain Current $R_{\theta JC}$ (Note 2)	Steady State	T_C = 25°C	I_D	61.3	A
		T_C = 100°C		43.4	
Power Dissipation $R_{\theta JC}$ (Note 2)		T_C = 25°C	P_D	107.1	W
		T_C = 100°C		53.6	
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2)	Steady State	T_A = 25°C	I_D	10.5	A
		T_A = 100°C		7.4	
Power Dissipation $R_{\theta JA}$ (Notes 1, 2)		T_A = 25°C	P_D	3.1	W
		T_A = 100°C		1.6	
Pulsed Drain Current	T_A = 25°C, t_p = 10 μs		I_{DM}	382	A
Operating Junction and Storage Temperature Range			T_J, T_{stg}	−55 to +175	°C
Source Current (Body Diode)			I_S	89.3	A
Single Pulse Drain−to−Source Avalanche Energy ($I_{L(pk)}$ = 4.4 A)			E_{AS}	1301	mJ
Lead Temperature for Soldering Purposes (1/8″ from case for 10 s)			T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
1. Surface−mounted on FR4 board using a 650 mm², 2 oz. Cu pad.
2. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.

ON Semiconductor®

$V_{(BR)DSS}$	$R_{DS(ON)}$ MAX	I_D MAX
150 V	15 mΩ @ 10 V	61.3 A
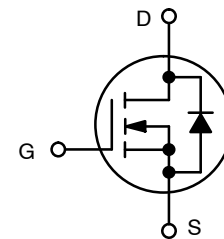
N−CHANNEL MOSFET

MARKING DIAGRAM

DPAK
CASE 369C

```
    4
  Drain

AYWW
015
N15MCG

 1        3
Gate    Source
    2
  Drain
```
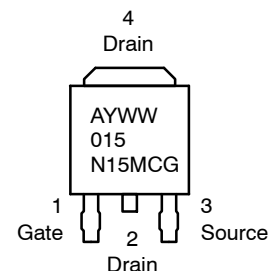
015N15MCG = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping[†]
NVDS015N15MCT4G	DPAK (Pb−Free)	2500 / Tube

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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NVDS015N15MC

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction−to−Case − Steady State (Note 2)	$R_{\theta JC}$	1.4	°C/W
Junction−to−Ambient − Steady State (Notes 1, 2)	$R_{\theta JA}$	47.9	

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 μA		150			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	I_D = 250 μA, ref to 25°C			83		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = 120 V	T_J = 25°C			1.0	μA
			T_J = 125°C		1.1		
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V				±100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = 162 μA		2.5		4.5	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$	I_D = 162 μA, ref to 25°C			−8.2		mV/°C
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 29 A			11.8	15	mΩ
Forward Transconductance	g_{FS}	V_{DS} = 10 V, I_D = 29 A			58		S
CHARGES, CAPACITANCES & GATE RESISTANCE							
Input Capacitance	C_{ISS}	V_{GS} = 0 V, f = 1 MHz, V_{DS} = 75 V			2120		pF
Output Capacitance	C_{OSS}				595		
Reverse Transfer Capacitance	C_{RSS}				10.5		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 10 V, V_{DS} = 75 V; I_D = 29 A			27		nC
Threshold Gate Charge	$Q_{G(TH)}$				7		
Gate−to−Source Charge	Q_{GS}				11		
Gate−to−Drain Charge	Q_{GD}				4		
Plateau Voltage	V_{GP}				5.5		V
SWITCHING CHARACTERISTICS (Note 3)							
Turn−On Delay Time	$t_{d(ON)}$	V_{GS} = 10 V, V_{DD} = 75 V, I_D = 29 A, R_G = 6 Ω			16		ns
Rise Time	t_r				5		
Turn−Off Delay Time	$t_{d(OFF)}$				21		
Fall Time	t_f				4		
DRAIN−SOURCE DIODE CHARACTERISTICS							
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = 29 A	T_J = 25°C		0.89	1.2	V
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, V_{DD} = 75 V dI_S/dt = 300 A/μs, I_S = 29 A			49		ns
Reverse Recovery Charge	Q_{RR}				197		nC
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, V_{DD} = 75 V dI_S/dt = 1000 A/μs, I_S = 29 A			34		ns
Reverse Recovery Charge	Q_{RR}				345		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
3. Switching characteristics are independent of operating junction temperatures.
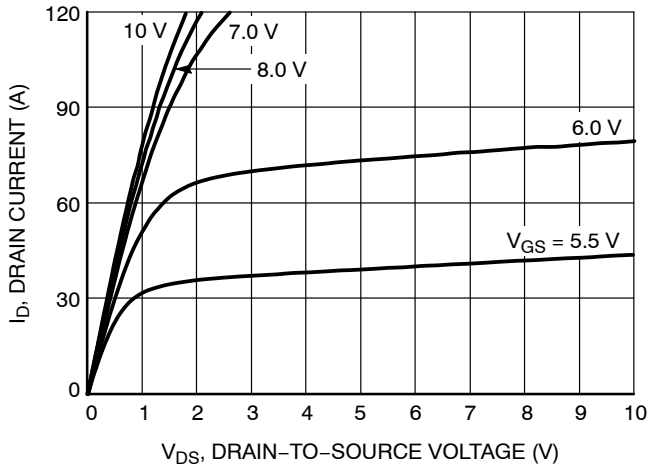
NVDS015N15MC

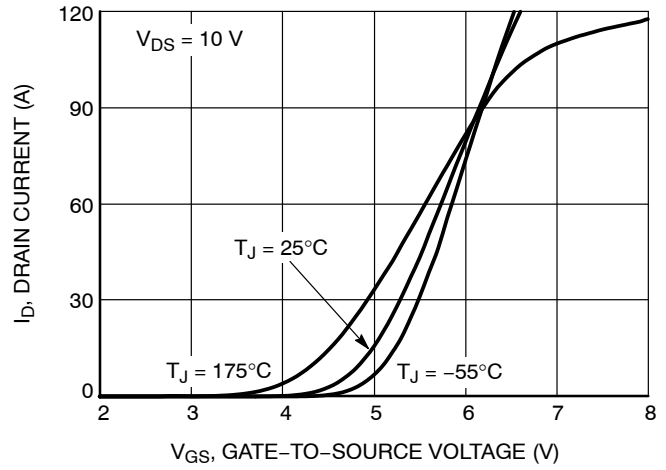## TYPICAL CHARACTERISTICS

Figure 1. On−Region Characteristics

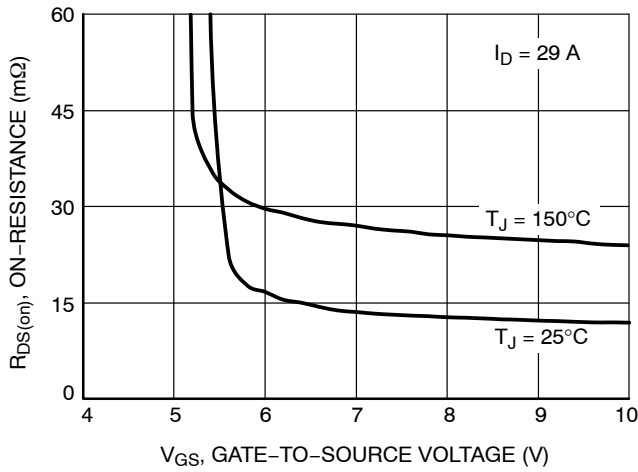**Figure 2. Transfer Characteristics**

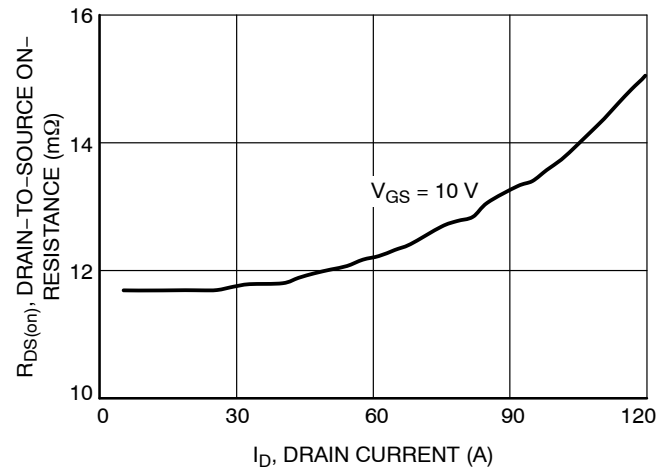**Figure 3. On−Resistance vs. Gate−to−Source Voltage**

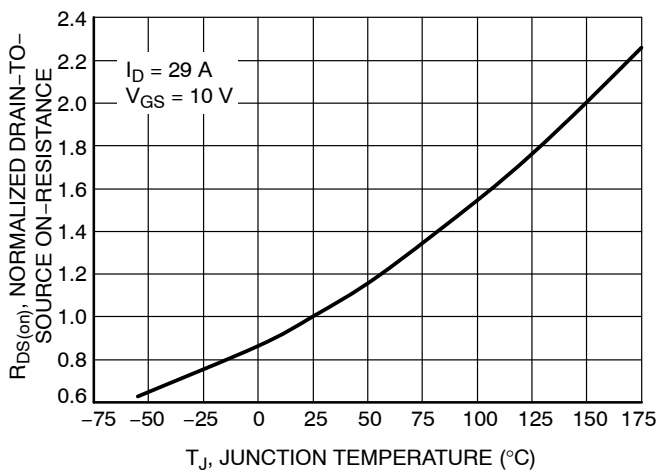**Figure 4. On−Resistance vs. Drain Current and Gate Voltage**

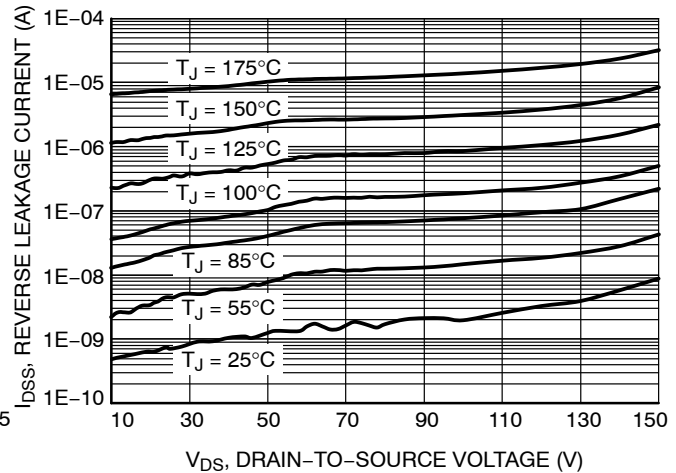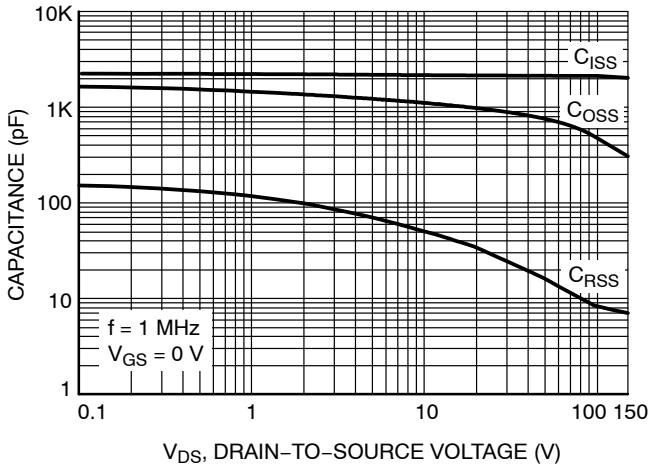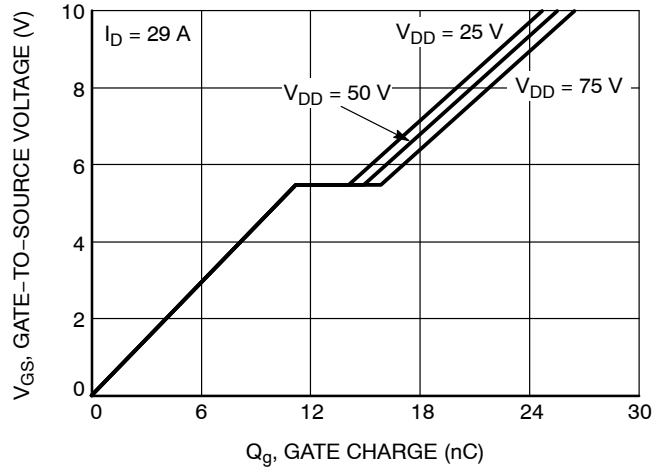**Figure 5. Normalized On−Resistance vs. Junction Temperature**

Figure 6. Drain−to−Source Leakage Current vs. Voltage
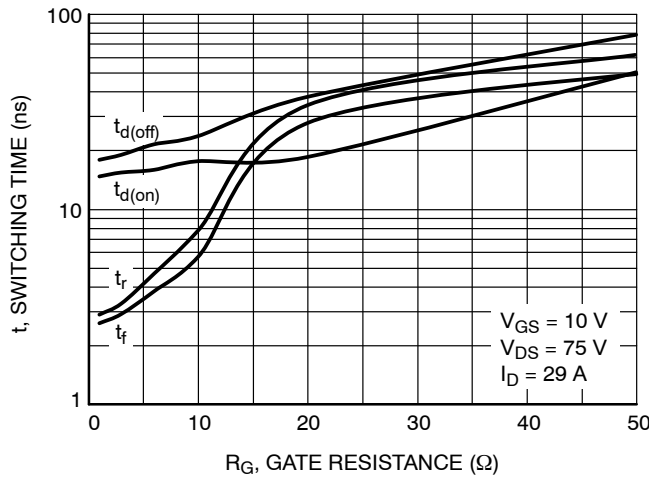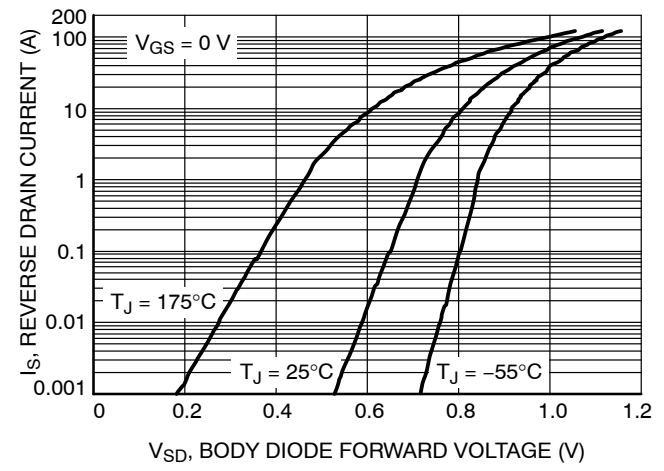
TYPICAL CHARACTERISTICS

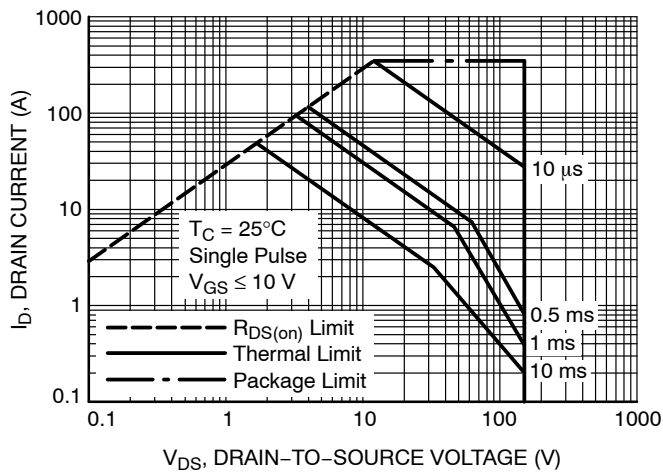**Figure 7. Capacitance vs. Drain−to−Source Voltage**

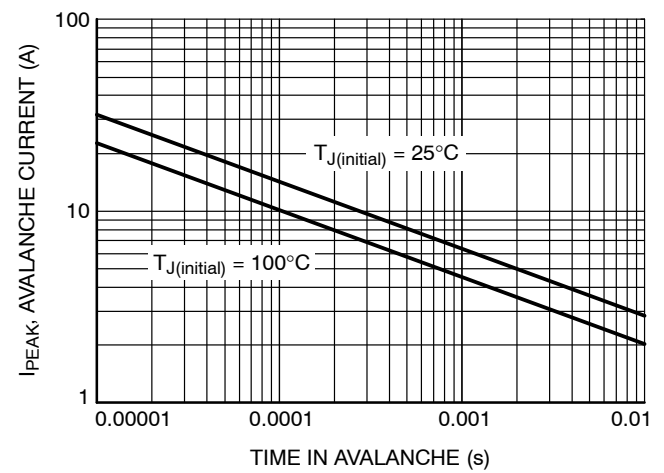**Figure 8. Gate Charge Characteristics**

Figure 9. Resistive Switching Time Variation vs. Gate Resistance

Figure 10. Source−to−Drain Diode Forward Voltage vs. Source Current

Figure 11. Forward Bias Safe Operating Area

Figure 12. Unclamped Inductive Switching Capability

TYPICAL CHARACTERISTICS

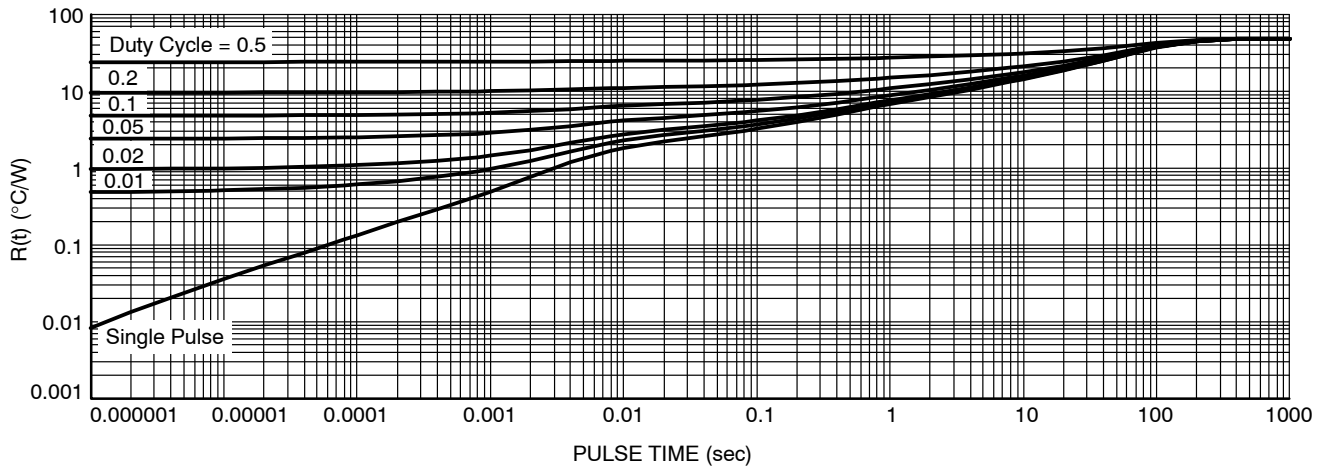**Figure 13. Transient Thermal Impedance**

DPAK (SINGLE GAUGE)
CASE 369C
ISSUE G

DATE 31 MAY 2023

SCALE 1:1

NOTES:
1. DIMENSIONING AND TOLERANCING ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3, AND Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
7. OPTIONAL MOLD FEATURE.

TOP VIEW

SIDE VIEW

DETAIL A

BOTTOM VIEW

BOTTOM VIEW
ALTERNATE CONSTRUCTIONS

DIM	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090 BSC		2.29 BSC	
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114 REF		2.90 REF	
L2	0.020 BSC		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4	----	0.040	---	1.01
Z	0.155	----	3.93	---

5.80 [0.228]

6.20 [0.244]

2.58 [0.102]

3.00 [0.118]

1.60 [0.063]

6.17 [0.243]

DETAIL A
ROTATED 90° CW

RECOMMENDED MOUNTING FOOTPRINT*

*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

GENERIC MARKING DIAGRAM*

XXXXXXG
ALYWW

AYWW
XXX
XXXXXG

IC   **Discrete**

XXXXXX = Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
WW = Work Week
G = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 3:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

STYLE 4:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

STYLE 5:
PIN 1. GATE
2. ANODE
3. CATHODE
4. ANODE

STYLE 6:
PIN 1. MT1
2. MT2
3. GATE
4. MT2

STYLE 7:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 8:
PIN 1. N/C
2. CATHODE
3. ANODE
4. CATHODE

STYLE 9:
PIN 1. ANODE
2. CATHODE
3. RESISTOR ADJUST
4. CATHODE

STYLE 10:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. ANODE

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